

## **FRED Module**

Preliminary

 $V_{RRM} = 600 \text{ V}$ 

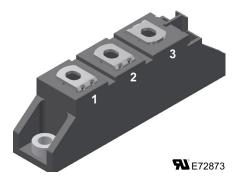
 $I_{FAV} = 95 A$ 

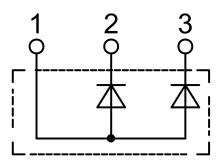
 $t_{xx} = 35 \, \text{ns}$ 

# Fast Recovery Epitaxial Diode Common Anode

#### Part number

MPA 95-06DA





### Features / Advantages:

- Planar passivated chips
- · Low switching losses
- · Soft recovery behaviour
- · High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- · Low noise switching
- Low losses

#### **Applications:**

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- · Ultrasonic cleaners and welders

Package: TO-240AA

- Isolation voltage: 4800 V~
- · Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- · Advanced power cycling

#### Disclaimer Notice

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## Preliminary

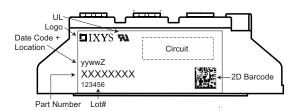
Diode					Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.		
V <sub>RSM</sub>	max. non-repetitive reverse blocking volt	age	$T_{VJ} = 25^{\circ}C$			600	V	
V <sub>RRM</sub>	max. repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			600	V	
I <sub>FRMS</sub>	RMS forward current					200	Α	
I <sub>FAV</sub> ①	average forward current	sine 180°	T <sub>C</sub> = 110°C			95	Α	
I <sub>FSM</sub>	max. surge forward current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1200	Α	
P <sub>tot</sub>			$T_{C} = 25^{\circ}C$			215	W	
I <sub>R</sub>	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}C$ $T_{VJ} = 125^{\circ}C$			1.3 5	mA mA	
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 50 A I <sub>F</sub> = 100 A	$T_{VJ} = 25^{\circ}C$ $T_{VJ} = 125^{\circ}C$ $T_{VJ} = 25^{\circ}C$ $T_{VJ} = 25^{\circ}C$ $T_{VJ} = 125^{\circ}C$			1.73 1.22 1.89 1.40	V V V	
V <sub>T0</sub>	threshold voltage slope resistance	for power-loss calculations only	$T_{VJ} = T_{VJM}$			0.98 2.3	V mΩ	
R <sub>thJC</sub>	thermal resistance junction to case thermal resistance junction to heatsink				0.1	0.575	K/W K/W	
t <sub>rr</sub>	max. reverse recovery current	$I_F = 1 \text{ A; } V_R = 30 \text{ V; -di/dt} = 300 \text{ A/µs}$	$T_{VJ} = 25^{\circ}C$		35		ns	
I <sub>RM</sub>	reverse recovery time	$I_{_{\rm F}}$ = 130 A; $V_{_{\rm R}}$ = 100 V -di/dt = 300 A/ $\mu$ s; L $\leq$ 0.05 $\mu$ H	$T_{VJ} = 25^{\circ}C$ $T_{VJ} = 100^{\circ}C$		5.5	4.0 6.8	A A	
① I <sub>FAVM</sub> rat	ing includes reverse blocking losses at T <sub>v.JI</sub>	, V <sub>R</sub> = 0.8 V <sub>RRM</sub> , duty cycle d = 0.5				,		





## Preliminary

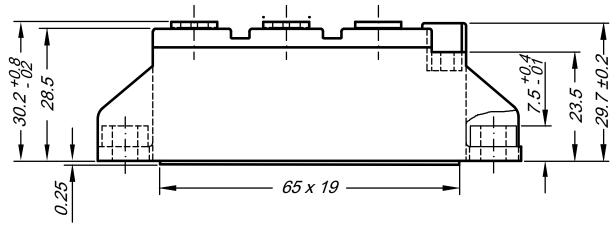
Package	TO-240AA				Ratings				
Symbol	Definitions	Conditions				min.	typ.	max.	
RMS	RMS current	per terminal						200	Α
T <sub>vJ</sub>	virtual junction temperature				-40		150	°C	
T <sub>op</sub>	operation temperature				-40		125	°C	
T <sub>stg</sub>	storage temperature			-40		125	°C		
Weight							76		g
M <sub>D</sub>	mounting torque			2.5		4	Nm		
M <sub>T</sub>	terminal torque				2.5		4	Nm	
d <sub>Spp/App</sub>	creepage distance on surface   striking distance through air		oir	terminal to terminal	13.0	9.7			mm
d <sub>Spb/Apb</sub>			all	terminal to backside	16.0	16.0			mm
V <sub>ISOL</sub>	isolation voltage t = 1 second					4800			V
		t = 1 minute $50/60 \text{ Hz}$ , RMS; $I_{ISOL} \le 1 \text{ mA}$			4000			V	



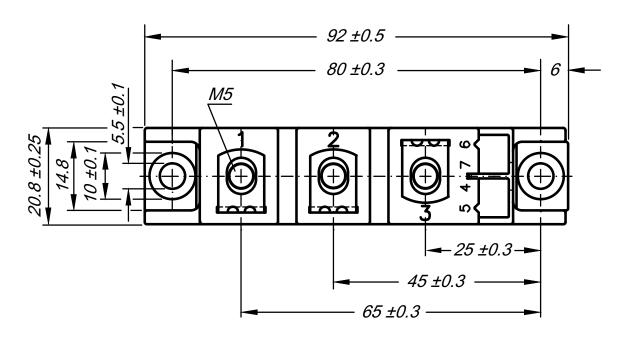
**Preliminary** 

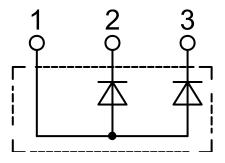
**Outlines TO-240AA** 

Dimensions in mm (1 mm = 0.0394")



General tolerance: DIN ISO 2768 class "c"





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